

## CLAIMS AMENDMENTS

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device comprising:  
a semiconductor chip having a planar active surface including an integrated circuit protected by an inorganic overcoat, said circuit having metallization patterns including a plurality of contact pads; and  
each of said contact pads having an added conductive layer on said metallization, said added layer having a conformal surface adjacent said chip, including peripheral portions of said overcoat, and a planar outer surface defining a flat outline, said outer surface suitable to form metallurgical bonds without melting.
2. (Currently Amended) The device according to claim 1 further comprising:  
a non-conductive adhesive layer over said overcoat, filling the spaces between said added conductive layers on each of said contact pads; and  
wherein the planar outer surface defining a flat outline is substantially parallel to the chip surface.
3. (Withdrawn)
4. (Original) The device according to claim 1 wherein said chip metallization is aluminum, copper, or alloys thereof.
5. (Original) The device according to claim 1 wherein said conductive layer consists of at least two conductive sub-layers, one being a conductive diffusion barrier, the other, outer layer being bondable.
6. (Original) The device according to claim 1 wherein said conductive diffusion barrier is selected from a group consisting of nickel, vanadium, titanium, tungsten, tantalum, osmium, chromium, and aluminum.

7. (Original) The device according to claim 1 wherein said bondable layer is selected from a group consisting of gold, palladium, platinum, silver, and alloys thereof.
8. (Original) The device according to claim 1 wherein said outer surface has a flatness suitable for metal interdiffusion with another flat surface formed by a metal suitable for interdiffusion.
9. (Original) The device according to claim 1 wherein said inorganic overcoat is moisture impermeable and stiff.
10. (Withdrawn)
11. (Withdrawn)
12. (Withdrawn)
13. (Withdrawn)
14. (Withdrawn)
15. (Original) The device according to claim 1 wherein said semiconductor chip is made from a material selected from a group consisting of silicon, silicon germanium, gallium arsenide, and any other semiconductor material used in integrated circuit fabrication.
16. (Withdrawn)
17. (Withdrawn)
18. (Withdrawn)

19. (Withdrawn)
20. (Withdrawn)
21. (Withdrawn)
22. (Original) The device according to claim 1 further comprising a protective layer on the chip surface opposite said active surface, said protective layer shielding against light and disturbing environmental influences.
23. (Original) The device according to claim 22 wherein said protective layer comprises hardened polymeric material.
24. (Withdrawn)
25. (Withdrawn)
26. (Withdrawn)
27. (Withdrawn)
28. (Withdrawn)
29. (Withdrawn)
30. (Withdrawn)
31. (Withdrawn)
32. (Withdrawn)

33. (Withdrawn)

34. (Withdrawn)

35. (Withdrawn)

36. (Withdrawn)

37. (Withdrawn)

38. (Withdrawn)